## Vishay Semiconductors

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### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 x 8 A				
V <sub>R</sub>	200 V				
V <sub>F</sub> at I <sub>F</sub>	0.77 V				
t <sub>rr</sub>	27 ns				
T <sub>J</sub> max.	175 °C				
Package	SMPD (TO-263AC)				
Circuit configuration	Common cathode				

#### FEATURES

• Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



FREE

- 175 °C maximum operating junction temperature
- · Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, telecom, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

#### **MECHANICAL DATA**

Case: SMPD (TO-263AC)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V		
Average restified forward average	per device		T <sub>solder pad</sub> = 155 °C	16	٨		
Average rectified forward current	per diode	IF(AV)		8			
Non-repetitive peak surge current			T 05 °C 6 mg aguara pulas 190	А			
Non-repetitive peak surge current	per diode	IFSM	$T_J = 25 \ ^{\circ}C$ , 6 ms square pulse	100			

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \ ^{\circ}C$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	200	-	-		
Forward voltage, per diode		I <sub>F</sub> = 8 A	-	0.93	1.03	V	
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	0.77	0.87		
Devenue la classe commento a condicada	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	2		
Reverse leakage current, per diode		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	6	100	μΑ	
Junction capacitance, per diode	CT	V <sub>R</sub> = 200 V	-	23	-	pF	

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	õs, V <sub>R</sub> = 30 V	-	27	-	
Bayaraa raaayary tima	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$	-	-	25		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	23	-	ns
		T <sub>J</sub> = 125 °C	$I_F = 8 A,$	-	35	-	
Pools recovery ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.8	-	Α
Peak recovery current		T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs, V <sub>B</sub> = 160 V	-	5	-	~
Deverse version shows	0	T <sub>J</sub> = 25 °C		-	30	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	90	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	+175	°C	
Thermal resistance, per diode junction to mount	R <sub>thJM</sub>		-	1.8	2.5	°C/W	
Approximate weight				0.55		g	
Approximate weight				0.02		oz.	
Marking device		Case style SMPD (TO-263AC)		16CI	DH02		



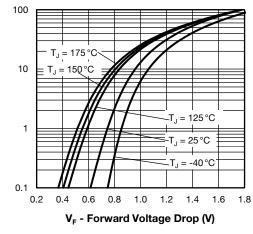


Fig. 1 - Typical Forward Voltage Drop Characteristics

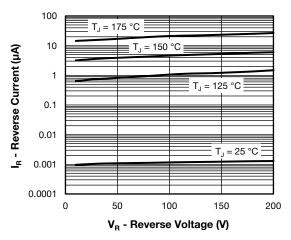


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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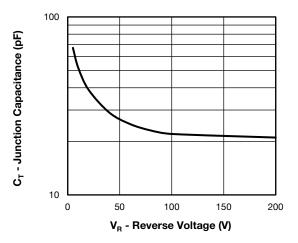


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

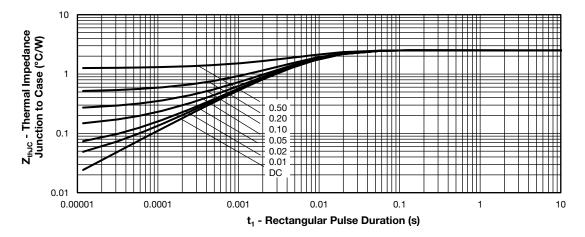
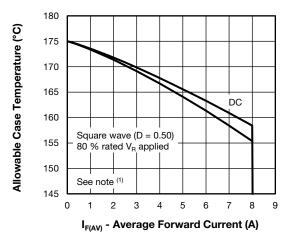
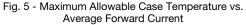


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/\mbox{D}) \mbox{ (see fig. 5);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); } \mbox{I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated} \mbox{V}_{R} \end{array}$ 

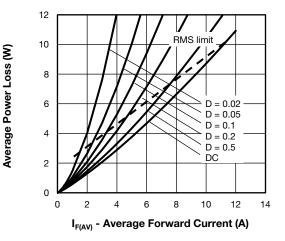


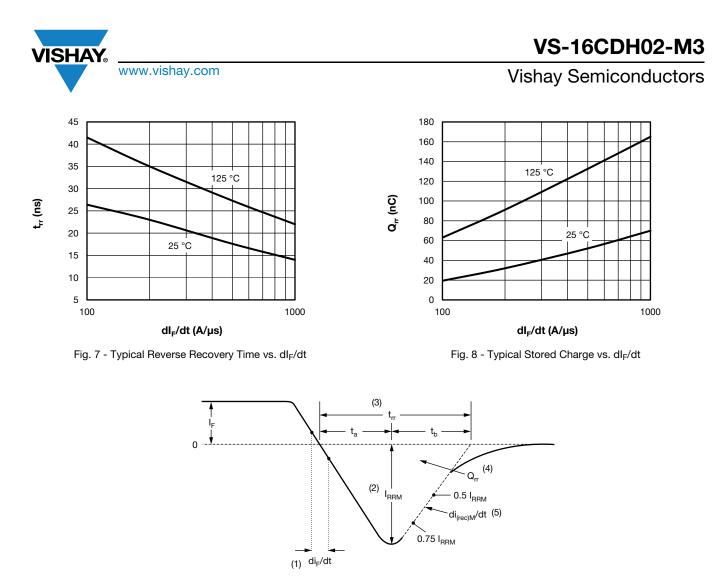
Fig. 6 - Forward Power Loss Characteristics

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- (2)  $I_{\text{RRM}}$  peak reverse recovery current
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$  extrapolated to zero current.
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) di<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

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### **ORDERING INFORMATION TABLE**

Device code	VS-	16	С	D	н	02	-M3
201100 0000			•			02	
	1	2	3	4	5	6	7
	1	- Visł	nay Sem	nicondu	ctors pr	oduct	
	2	- Cur	rent rati	ng (16 A	A)		
	3	- Circ	cuit conf	figuratio	n:		
		C =	commo	on catho	de		
	4	- D =	SMPD	packag	e		
	5	- Pro	cess typ	be,			
		H =	hyperfa	ast recov	very		
	6	- Volt	tage coo	de (02 =	200 V)		
	7	M3	3 = halo	gen-free	e, RoHS	-compli	iant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-16CDH02-M3/I	2000	2000	13" diameter plastic tape and reel				

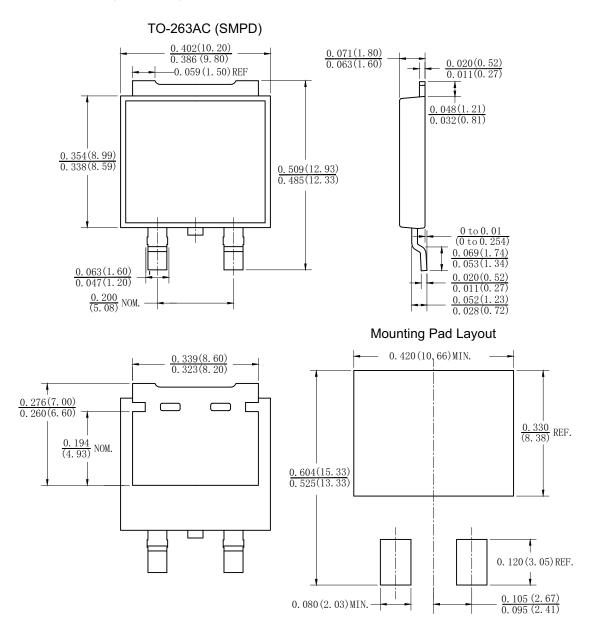
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95604				
Part marking information	www.vishay.com/doc?95566				
Packaging information	www.vishay.com/doc?88869				





TO-263AC (SMPD)

#### **DIMENSIONS** in inches (millimeters)





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